Silicon PNP Power Transistors BD318

DESCRIPTION

·With TO-3 package
·High DC current gain
·Excellent safe operating area
·Complement to type BD317

APPLICATIONS

·Designed for high power amplifiers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

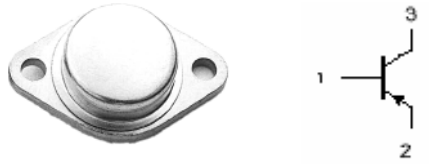

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-16	A
I_{CM}	Collector current(peak)		-20	A
I_B	Base current		-5	A
P_T	Total power dissipation	T_C=25□	200	W
T_j	Junction temperature		-65~200	□
T_{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance from junction to case	0.875	□/W

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=-0.2A ; I_B=0	-100			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-8A ;I_B=-0.8A			-1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-8A ;I_B=-0.8A			-1.8	V
$V_{BE(on)}$	Base-emitter on voltage	I_C=-8A ;V_{CE}=-2.0V			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=100V;I_E=0			-1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-7V; I_C=0			-1.0	mA
h_{FE-1}	DC current gain	I_C=-5A ; V_{CE}=-4V	25			
h_{FE-2}	DC current gain	I_C=-10A ; V_{CE}=-4V	15			
f_T	Transition frequency	I_C=-1A ; V_{CE}=-20V,f=0.2MHz	1			MHz

PACKAGE OUTLINE

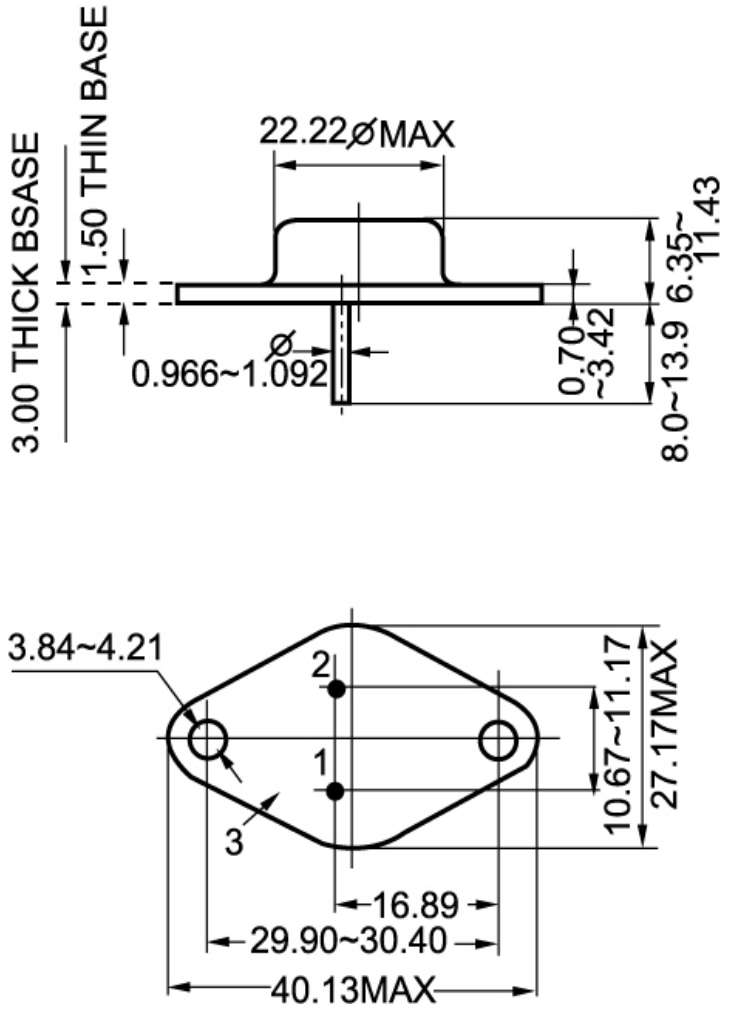

Fig.2 Outline dimensions